

March 2000

FDN5630

60V N-Channel PowerTrench® MOSFET

General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

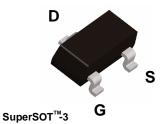
This MOSFET features very low $R_{\rm DS(ON)}$ in a small SOT23 footprint. Fairchild's PowerTrench technology provides faster switching than other MOSFETs with comparable $R_{\rm DS(ON)}$ specifications. The result is higher overall efficiency with less board space.

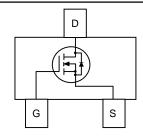
Features

- 1.7 A, 60 V. $R_{DS(ON)} = 0.100 \Omega$ @ $V_{GS} = 10 V$ $R_{DS(ON)} = 0.120 \Omega$ @ $V_{GS} = 6 V$.
- Optimized for use in high frequency DC/DC converters.
- Low gate charge.
- · Very fast switching.
- SuperSOTTM 3 provides low $R_{\mathrm{DS(ON)}}$ in SOT23 footprint.

Applications

- DC/DC converter
- Motor drives





Absolute Maximum Ratings T_A = 25 C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V _{DSS}	Drain-Source Voltage	60	V	
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Drain Current - Continuous	(Note 1a)	1.7	Α
	- Pulsed		10	
P _D	Power Dissipation for Single Operation	(Note 1a)	0.5	W
		(Note 1b)	0.46	1
T _J , T _{stg}	Operating and Storage Junction Temperature	-55 to +150	°C	

Thermal Characteristics

$R_{\theta}JA$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	250	°C/W
R _e JC	Thermal Resistance, Junction-to-Case	(Note 1)	75	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity	
5630	FDN5630	7	8mm	3000 units	

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Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Char	acteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
<u>ΔBV_{DSS}</u> ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to $25^{\circ}C$		63		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 48 V, V _{GS} = 0 V			1	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Char	acteristics (Note 2)					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	1	2.4	3	V
$\Delta V_{GS(th)} = \Delta T_J$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$, Referenced to $25^{\circ}C$		6.9		mV/°C
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 10 \text{ V}, I_D = 1.7 \text{ A}$ $V_{GS} = 10 \text{ V}, I_D = 1.7 \text{ A}, T_J = 125^{\circ}\text{C}$ $V_{GS} = 6 \text{ V}, I_D = 1.6 \text{ A}$		0.073 0.127 0.083	0.100 0.180 0.120	Ω
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 1.7 V	5			Α
g FS	Forward Transconductance	V _{DS} = 10 V, I _D = 1.7 A		6		S
Dynamic	Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		400		pF
Coss	Output Capacitance	f = 1.0 MHz		102		pF
C _{rss}	Reverse Transfer Capacitance			21		pF
Switchin	g Characteristics (Note 2)	•	•	!		
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, I_D = 1 \text{ A},$		10	20	ns
t _r	Turn-On Rise Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$		6	15	ns
t _{d(off)}	Turn-Off Delay Time			15	28	ns
t _f	Turn-Off Fall Time			5	15	ns
Qg	Total Gate Charge	V _{DS} = 20 V, I _D = 1.7 A,		7	10	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V,		1.6		nC
Q _{gd}	Gate-Drain Charge	1		1.2		nC
Drain-So	urce Diode Characteristics a	and Maximum Ratings	•			•
ls	Maximum Continuous Drain-Source				0.42	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 0.42 A (Note 2)		0.72	1.2	V

1: $R_{a,JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{a,JC}$ is guaranteed by design while $R_{a,JA}$ is determined by the user's board design.



a) 250°C/W when mounted on a 0.02 in² Pad of 2 oz. Cu.



b) 270°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper 2: Pulse Test: Pulse Width $\leq\!300~\mu\text{s},$ Duty Cycle $\leq\!2.0\%$

Typical Characteristics

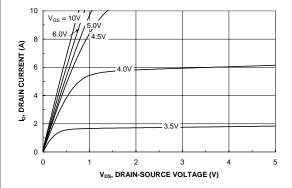


Figure 1. On-Region Characteristics.

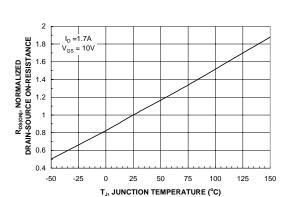


Figure 3. On-Resistance Variation with Temperature.

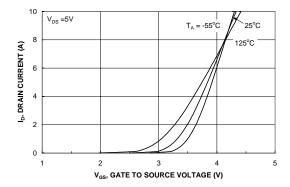


Figure 5. Transfer Characteristics.

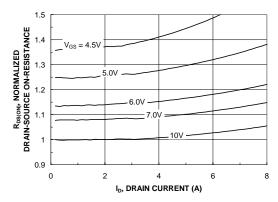


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

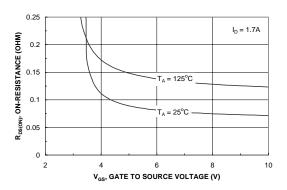


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

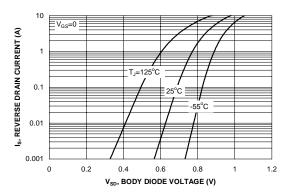
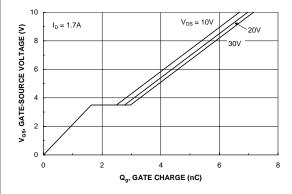


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)



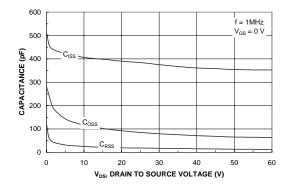
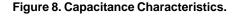
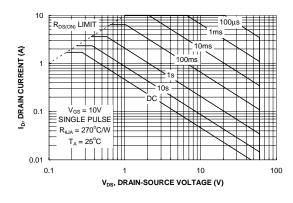


Figure 7. Gate Charge Characteristics.





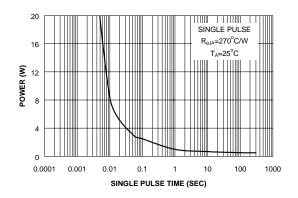


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

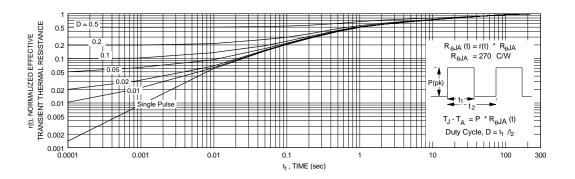
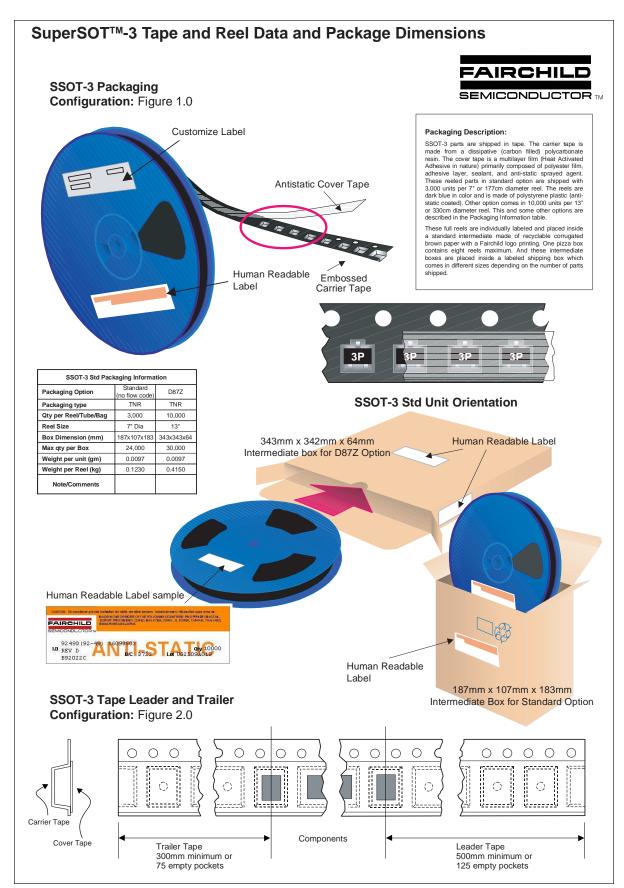
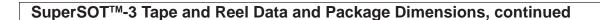


Figure 11. Transient Thermal Response Curve.

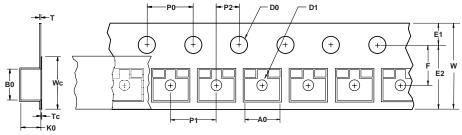
Thermal characterization performed using the conditions described in Note 1b. Transient themal response will change depending on the circuit board design.





SSOT-3 Embossed Carrier Tape

Configuration: Figure 3.0



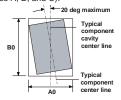


	Dimensions are in millimeter													
Pkg type	A0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SSOT-3 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-02

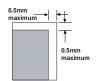
Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



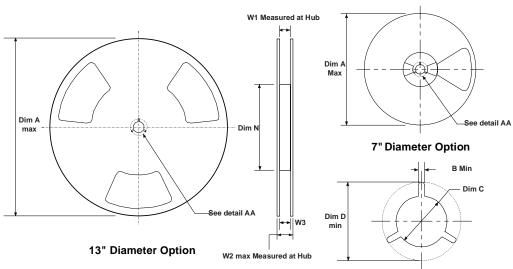
Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

DETAIL AA

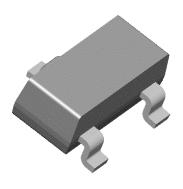
SSOT-3 Reel Configuration: Figure 4.0

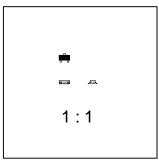


	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	

SuperSOT™-3 Tape and Reel Data and Package Dimensions, continued

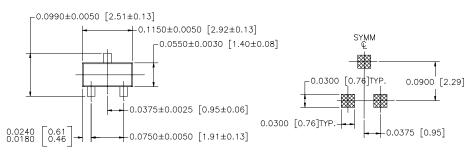
SuperSOT™-3 (FS PKG Code 32)



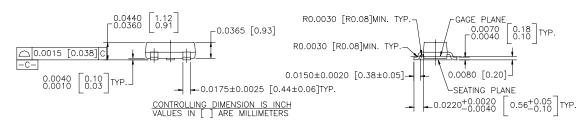


Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0097



LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

SUPER SOT , 3 LEADS

- 1. STANDARD LEAD FINISH TO BE 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN/LEAD (SOLDER) ON COPPER.
- 2. NO JEDEC REGISTRATION AS OF DEC. 1995.



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